

SEMiX604GB12E4s



Trench IGBT Modules

SEMiX604GB12E4s

Features

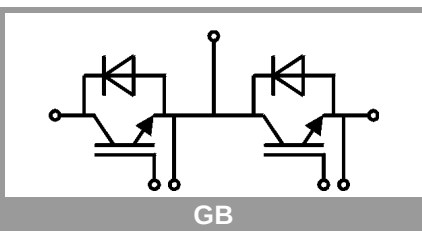
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability
- UL recognized, file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic Welding

Remarks

- Case temperature limited to $T_C=125^{\circ}\text{C}$ max.
- Product reliability results are valid for $T_J=150^{\circ}\text{C}$
- Dynamic values apply to the following combination of resistors:
 $R_{Gon,main} = 1,0 \Omega$
 $R_{Goff,main} = 6,2 \Omega$
 $R_{G,X} = 2,2 \Omega$
 $R_{E,X} = 0,5 \Omega$



Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
IGBT				
V _{CES}			1200	V
I _C	T _j = 175 °C	T _c = 25 °C	916	A
		T _c = 80 °C	704	A
I _{Cnom}			600	A
I _{CRM}	I _{CRM} = 3xI _{Cnom}		1800	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 800 V V _{GE} ≤ 20 V V _{CES} ≤ 1200 V	T _j = 150 °C	10	µs
T _j			-40 ... 175	°C
Inverse diode				
I _F	T _j = 175 °C	T _c = 25 °C	707	A
		T _c = 80 °C	529	A
I _{Fnom}			600	A
I _{FRM}	I _{FRM} = 3xI _{Fnom}		1800	A
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 25 °C		3240	A
T _j			-40 ... 175	°C
Module				
I _{t(RMS)}			600	A
T _{stg}			-40 ... 125	°C
V _{isol}	AC sinus 50Hz, t = 1 min		4000	V

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
IGBT						
V _{CE(sat)}	I _C = 600 A	T _j = 25 °C		1.8	2.05	V
	V _{GE} = 15 V chipelevel	T _j = 150 °C		2.2	2.4	V
V _{CE0}		T _j = 25 °C		0.8	0.9	V
		T _j = 150 °C		0.7	0.8	V
r _{CE}	V _{GE} = 15 V	T _j = 25 °C		1.7	1.9	mΩ
		T _j = 150 °C		2.5	2.7	mΩ
V _{GE(th)}	V _{GE} =V _{CE} , I _C = 24 mA		5	5.8	6.5	V
I _{CES}	V _{GE} = 0 V	T _j = 25 °C		0.12	0.36	mA
	V _{CE} = 1200 V	T _j = 150 °C				mA
C _{ies}	V _{CE} = 25 V	f = 1 MHz		37.2		nF
C _{oes}	V _{GE} = 0 V	f = 1 MHz		2.32		nF
C _{res}		f = 1 MHz		2.04		nF
Q _G	V _{GE} = - 8 V...+ 15 V			3400		nC
R _{Gint}	T _j = 25 °C			1.25		Ω
t _{d(on)}	V _{CC} = 600 V	T _j = 150 °C		374		ns
t _r	I _C = 600 A	T _j = 150 °C		85		ns
E _{on}	R _{G on} = 1.7 Ω	T _j = 150 °C		35		mJ
t _{d(off)}	R _{G off} = 6.9 Ω	T _j = 150 °C		1277		ns
t _f	di/dt _{on} = 7100 A/μs	T _j = 150 °C		114		ns
E _{off}	di/dt _{off} = 6350 A/μs	T _j = 150 °C		110.4		mJ
R _{th(i-c)}	per IGBT				0.049	K/W

SEMiX604GB12E4s



SEMiX® 4s

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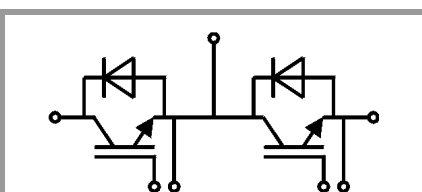
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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
V _F = V _{EC}	I _F = 600 A V _{GE} = 0 V chip	T _j = 25 °C		2.1	2.46	V
		T _j = 150 °C		2.1	2.4	V
V _{F0}		T _j = 25 °C	1.1	1.3	1.5	V
		T _j = 150 °C	0.7	0.9	1.1	V
r _F		T _j = 25 °C	1.1	1.4	1.6	mΩ
		T _j = 150 °C	1.7	1.9	2.1	mΩ
I _{RRM}	I _F = 600 A di/dt _{off} = 6000 A/μs V _{GE} = -15 V V _{CC} = 600 V	T _j = 150 °C	430			A
Q _{rr}		T _j = 150 °C	100			μC
E _{rr}		T _j = 150 °C	44			mJ
R _{th(j-c)}	per diode		0.086			K/W
Module						
L _{CE}			22			nH
R _{CC'+EE'}	res., terminal-chip	T _C = 25 °C	0.7			mΩ
		T _C = 125 °C	1			mΩ
R _{th(c-s)}	per module		0.03			K/W
M _s	to heat sink (M5)		3	5		Nm
M _t		to terminals (M6)	2.5	5		Nm
						Nm
w			400			g
Temperatur Sensor						
R ₁₀₀	T _c =100°C (R ₂₅ =5 kΩ)		493 ± 5%			Ω
B _{100/125}	R _(T) =R ₁₀₀ exp[B _{100/125} (1/T-1/T ₁₀₀)]; T[K];		3550 ±2%			K



GB

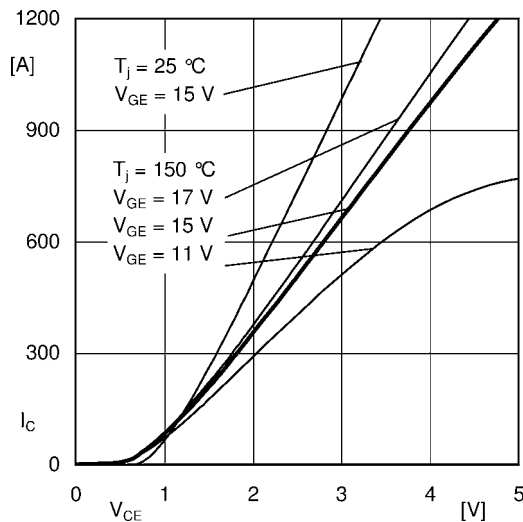


Fig. 1: Typ. output characteristic, inclusive $R_{CC'} + E_{E'}$

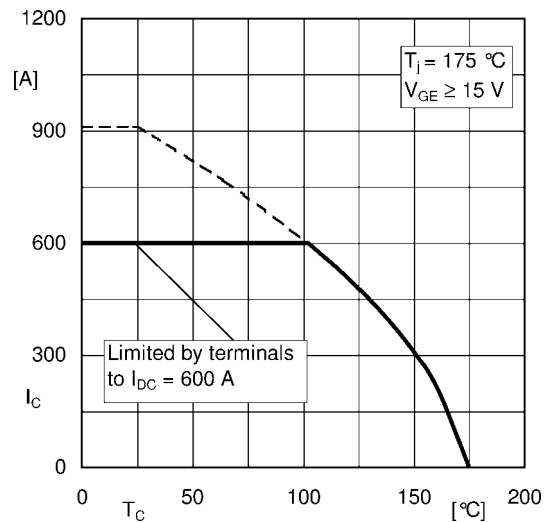


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

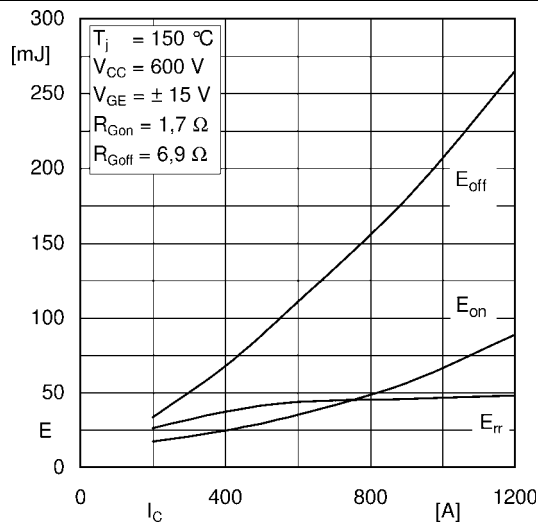


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

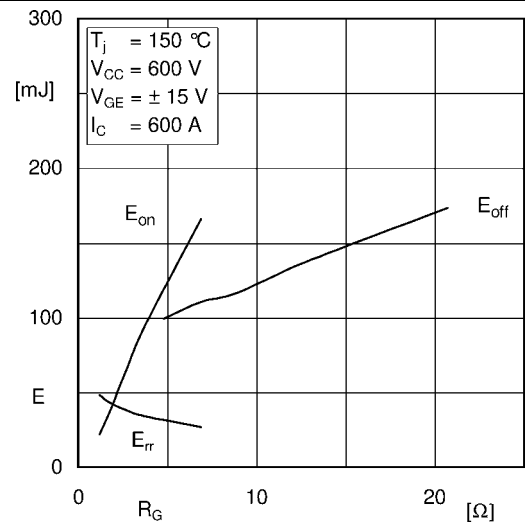


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

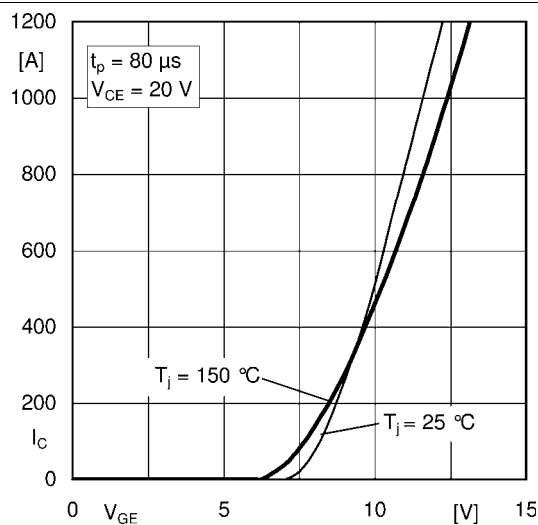


Fig. 5: Typ. transfer characteristic

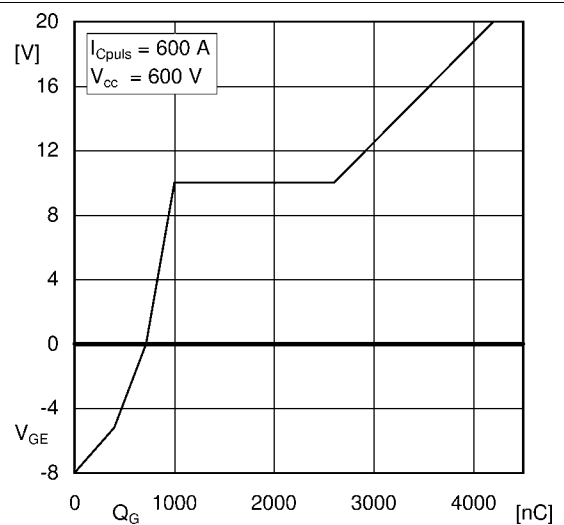


Fig. 6: Typ. gate charge characteristic

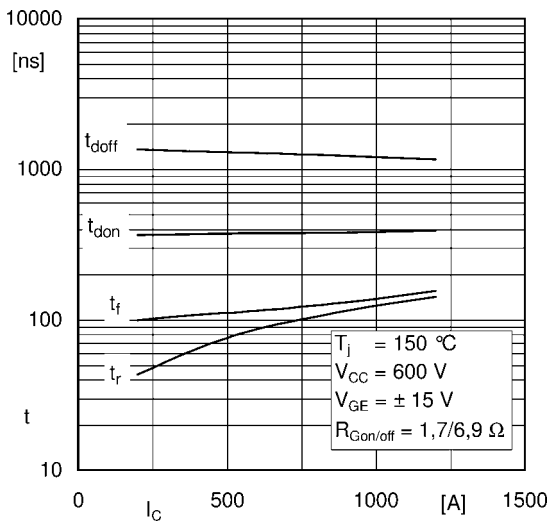


Fig. 7: Typ. switching times vs. I_C

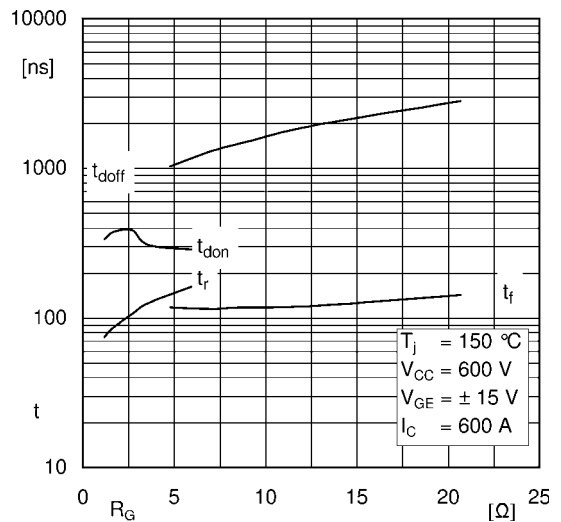


Fig. 8: Typ. switching times vs. gate resistor R_G

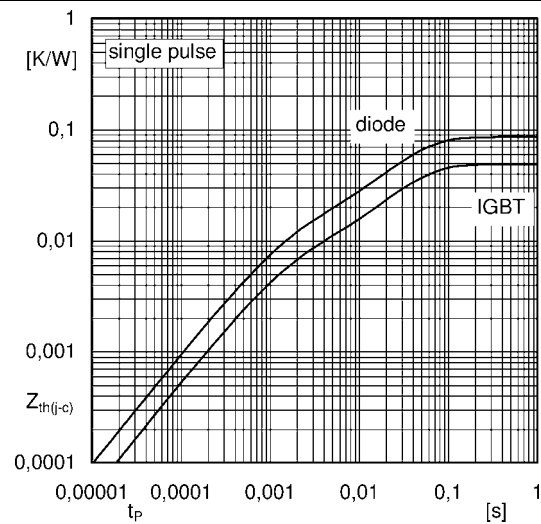


Fig. 9: Typ. transient thermal impedance

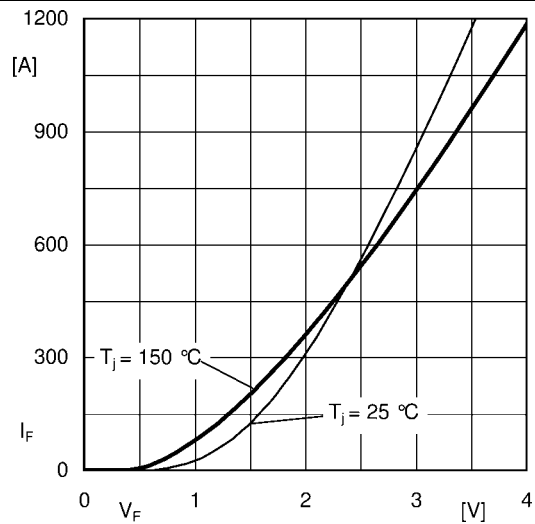


Fig. 10: Typ. CAL diode forward charact., incl. $R_{CC'+EE'}$

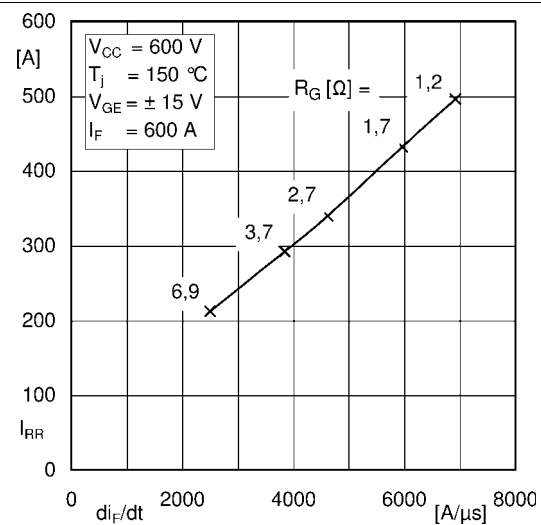


Fig. 11: Typ. CAL diode peak reverse recovery current

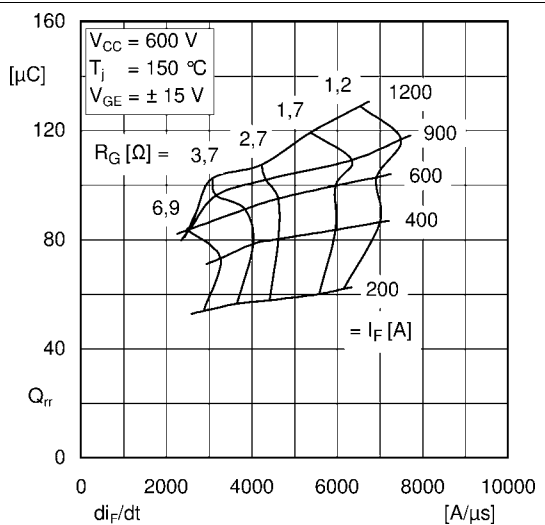
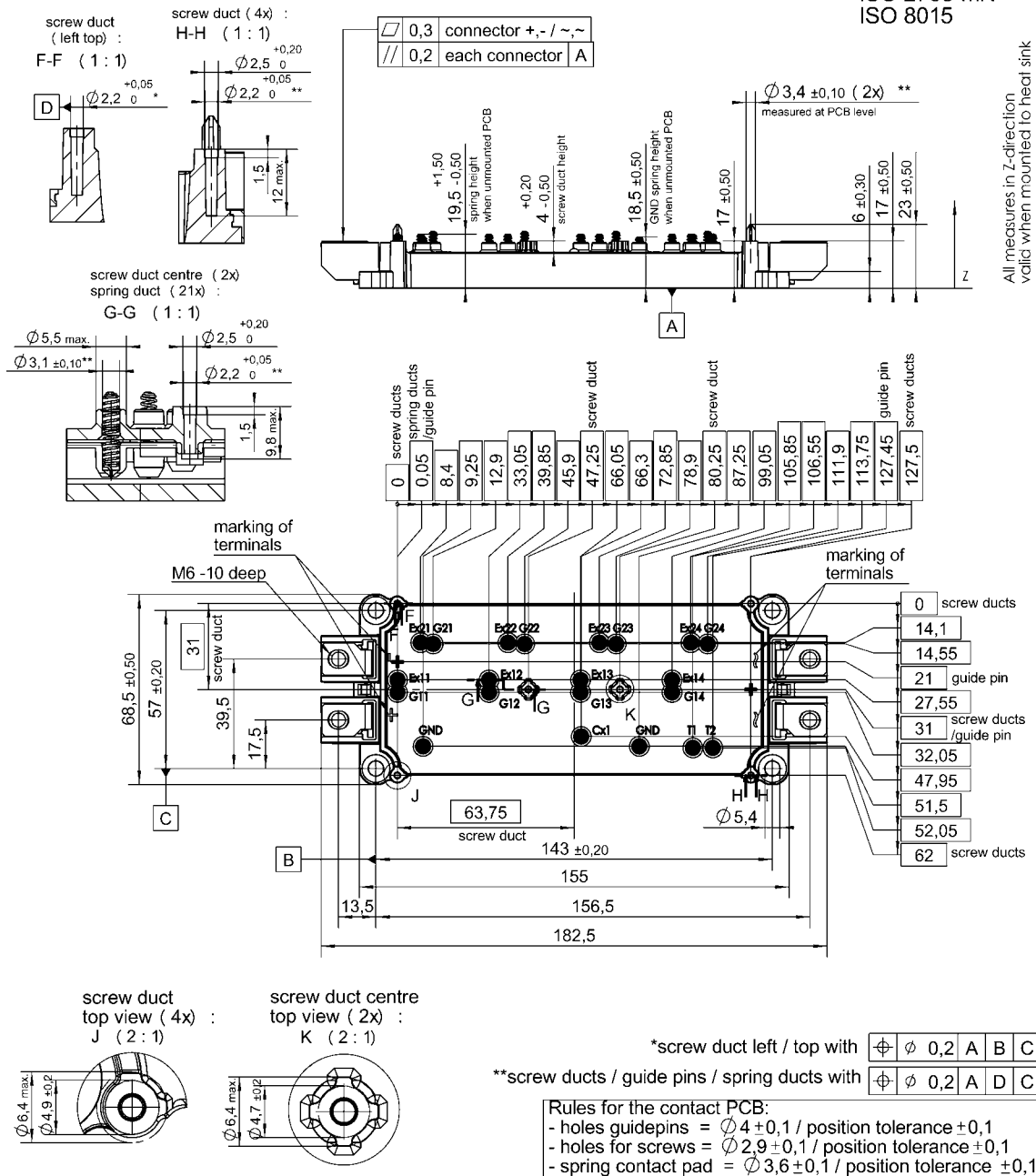


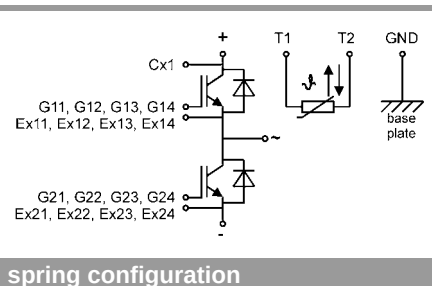
Fig. 12: Typ. CAL diode recovery charge

Case: SEMiX 4s

general tolerance:
ISO 2768-mK
ISO 8015



SEMiX 4s



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.